www.solidstateinc.com

PMD 16K, 17K SERIES

225 WATT (20 AMP CONTINUOUS, 40 AMP PEAK)



FEATURES

- Electrical specifications guaranteed for operating junction temperature range of 0 - 200°C
- Guaranteed and 100% tested for I_{SB} (Secondary Breakdown Current) insuring maximum performance at high energy levels
- Low thermal resistance for more useable power and lower operating temperatures
- Hermetically sealed

DESCRIPTION

The PMD 16K Series of devices are three-terminal NPN Darlington Power Transistors. The PMD 17K Series of devices are PNP Darlington Power Transistors. These devices are monolithic epitaxial base structures with built-in base to emitter shunt resistors. The devices are CVD glass passivated to increase reliability and provide reduced hightemperature reverse leakage current. This important feature enables this series of Darlington devices to meet guaranteed operating junction temperatures of 200°C. Internal diode protection (D1) of the Darlington configuration is built into the structure to limit the device power dissipation during negative overshoot.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	MAXIMUM	UNITS
Collector Emitter Voltage PMD16K, 17K80 PMD16K, 17K100	V _{CEO}	80 100	Vdc
Collector Base Voltage PMD16K, 17K80 PMD16K, 17K100	V _{CBO}	80 100	Vdc
Emitter Base Voltage	V _{EBO}	5	Vdc
Collector Current Continuous Peak	I _C	20 40	Adc
Base Current	l _B	0.5	Adc
Thermal Resistance	$\theta_{\sf JC}$	0.67	°C/Watt
Total Internal Power Dissipation @ T _C = 50°C¹	P _D	225	Watts
Operating Junction and Storage Temperature	T _J T _{STG}	-65 to +200	°C

⁽¹⁾ For operation above $T_c = 50$ °C, derate @ 1.5 W/°C.

DEVICE SELECTION GUIDE

DEVICE	VOLTAGE RATING	POLARITY	
PMD16K80	80V	NPN	
PMD16K100	100V	NPN	
PMD17K80	80V	PNP	
PMD17K100	100V	PNP	

Excellent thermal resistance junction to case (θ_{JC}) provides for more useable power at lower operating temperatures. This, coupled with 100% I_{SB} testing, insures optimum performance and durability for DC motor control and other complementary Darlington applications. These Darlington devices are hermetically sealed copper/steel TO-3 packages providing high reliability and low thermal resistance.

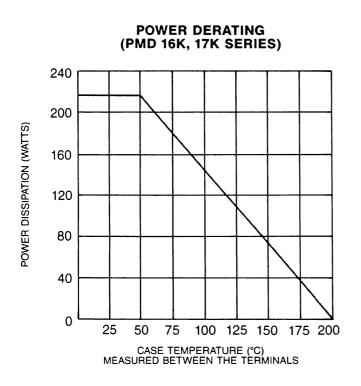
ELECTRICAL CHARACTERISTICS

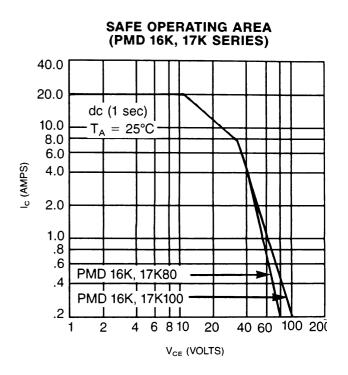
All parameters are guaranteed at $T_{J}=0$ to 200°C, unless otherwise specified.

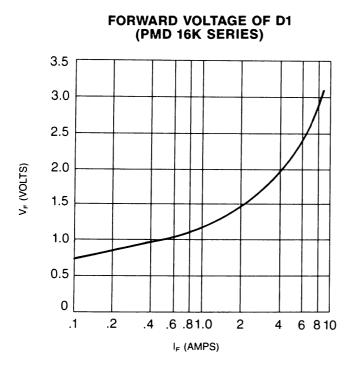
Parameter	Symbol	Test Conditions	Minimum	Maximum	Units
ON CHARACTERISTICS		4			1
Collector Emitter Saturation Voltage ¹	$V_{CE(sat)}$	$I_C = 10 \text{ Adc}; I_B = 40 \text{ mAdc}$		2.0	Vdc
Base Emitter Turn-on Voltage ¹	V _{BE(on)}	$I_C = 10 \text{ Adc}; V_{CE} = 3 \text{ Vdc}$		2.8	Vdc
Base Emitter Saturation ¹	V _{BE(sat)}	$I_C = 10 \text{ Adc}; I_B = 40 \text{ mAdc}$		2.8	Vdc
DC Current Gain ¹ PMD16K80, 100 PMD17K80, 100	h _{FE}	$I_C = 10 \text{ Adc}; V_{CE} = 3 \text{ Vdc}$ $T_J = 25^{\circ}\text{C}$	1000 800	20,000 20,000	
Forward Bias Secondary Breakdown Current	l _{s/b}	$V_{CE} = 30 \text{ Vdc}; T_A = 25^{\circ}\text{C}$ 1 sec non-repetitive pulse	7.5		Adc
OFF CHARACTERISTICS					
Collector Emitter Breakdown Voltage ¹ (Base Open)	V _{(BR)CEO}	$I_{CE} = 100 \text{ mAdc}; T_{J} = 25^{\circ}\text{C}$			Vdc
PMD16K, 17K80 PMD16K, 17K100			80 100		
Collector Emitter Sustaining Voltage ¹ PMD16K, 17K80 PMD16K, 17K100	V _{(SUS)CER}	$I_{CE}=100$ mAdc; $R_{BE}=2.2k\Omega$	80 100		Vdc
Emitter Base Leakage Current	I _{EBO}	$V_{EB} = 5 \text{ Vdc}; I_{C} = 0A$		3.0	mAdc
Collector Emitter Leakage Current	I _{CER}				mAdc
PMD16K, 17K80 PMD16K, 17K100		$V_{CE}=54$ Vdc; $R_{BE}=2.2k\Omega$ $V_{CE}=67$ Vdc; $R_{BE}=2.2k\Omega$		7.0 7.0	
DYNAMIC CHARACTERISTIC	S			!	·
Output Capacitance	Соь	$V_{CB} = 10 \text{ Vdc}; I_E = 0 \text{ Adc}$ $f = 1 \text{ MHz}; T_J = 25^{\circ}\text{C}$		400	pF
Small Signal Current Gain	h _{fe}	$I_C = 7$ Adc; $V_{CE} = 3$ Vdc f = 1 kHz; $T_J = 25^{\circ}$ C	300		
Common Emitter Short Circuit Forward Transfer Ratio	h _{fe}	$I_C = 7 \text{ Adc}; V_{CE} = 3 \text{ Vdc}$ $f = 1 \text{ MHz}; T_J = 25^{\circ}\text{C}$	4		

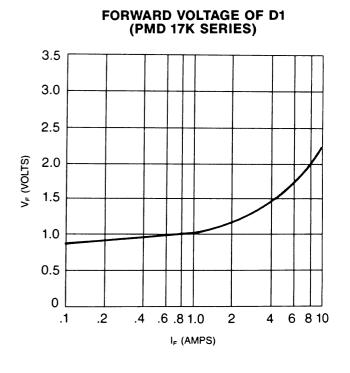
⁽¹⁾ Pulse tested with pulse width \leq 300 μS and duty cycle \leq 2.0%.

OPERATIONAL DATA



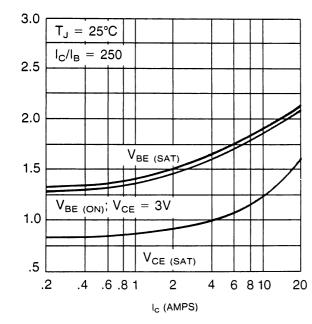






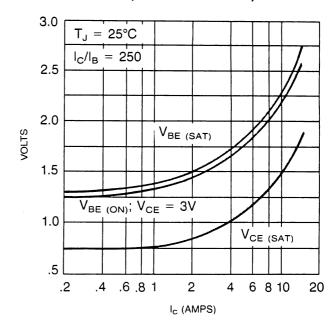
OPERATIONAL DATA



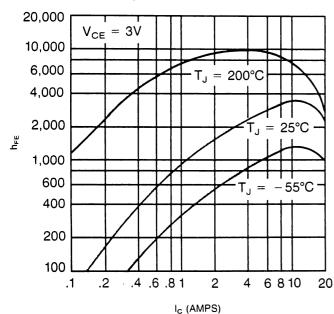


VOLTS

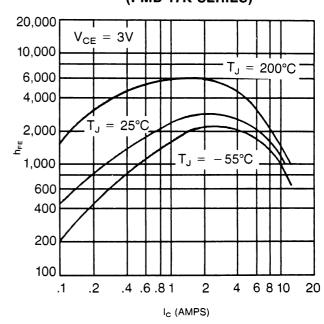
ON VOLTAGE VS COLLECTOR CURRENT (PMD 17K SERIES)



DC COLLECTOR CURRENT GAIN VS COLLECTOR CURRENT (PMD 16K SERIES)

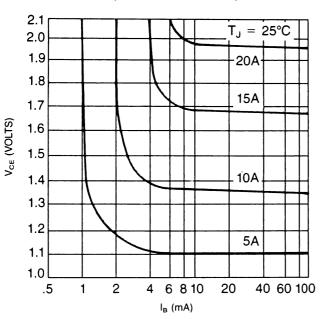


DC COLLECTOR CURRENT GAIN VS COLLECTOR CURRENT (PMD 17K SERIES)

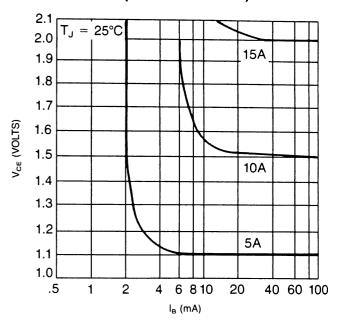


OPERATIONAL DATA

COLLECTOR SATURATION REGION (PMD 16K SERIES)

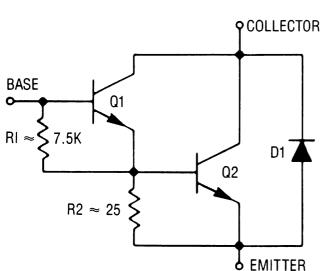


COLLECTOR SATURATION REGION (PMD 17K SERIES)

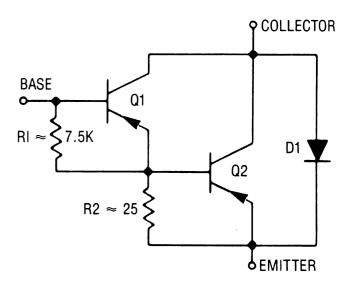


BLOCK DIAGRAMS

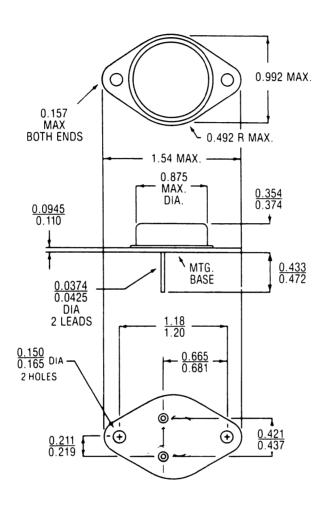
NPN



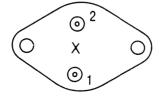
PNP



DEVICE OUTLINE



Bottom View



1 — Base2 — EmitterCase Is Collector